

Jian-Hao Chen

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/6933970/publications.pdf>

Version: 2024-02-01

56
papers

8,989
citations

257450

24
h-index

175258

52
g-index

56
all docs

56
docs citations

56
times ranked

11670
citing authors

#	ARTICLE	IF	CITATIONS
1	Repairable Polymer Solid Electrolyte Gated MoS ₂ Field Effect Devices with Large Radiation Tolerance. <i>Advanced Electronic Materials</i> , 2022, 8, 2100619.	5.1	3
2	A novel contact engineering method for transistors based on two-dimensional materials. <i>Journal of Materials Science and Technology</i> , 2021, 69, 15-19.	10.7	10
3	Circular photogalvanic effect from third-order nonlinear effect in 1Tâ€™-MoTe ₂ . <i>2D Materials</i> , 2021, 8, 025016.	4.4	8
4	Two superconductor-insulator phase transitions in the spinel oxide Li _{1-x} Ti ₂ O ₄ induced by ionic liquid gating. <i>Physical Review B</i> , 2021, 103, .	3.2	3
5	Electron-electron interactions and weak antilocalization in few-layer $ZrTe_2$ devices. <i>Physical Review B</i> , 2021, 103, .	3.2	3
6	Crossover behavior in the magnetoresistance of thin flakes of the topological material $ZrTe_2$. <i>Physical Review B</i> , 2021, 104, .	3.2	3
7	Enhancement of spin-orbit coupling and magnetic scattering in hydrogenated graphene. <i>Physical Review B</i> , 2021, 104, .	3.2	3
8	Gate-controlled magnetic transitions in Fe ₃ GeTe ₂ with lithium ion conducting glass substrate*. <i>Chinese Physics B</i> , 2021, 30, 097504.	1.4	6
9	Electrically switchable van der Waals magnon valves. <i>Nature Communications</i> , 2021, 12, 6279.	12.8	26
10	DyOCl: A rare-earth based two-dimensional van der Waals material with strong magnetic anisotropy. <i>Physical Review B</i> , 2021, 104, .	3.2	13
11	Anisotropic Raman spectrum and transport properties of AuTe ₂ Br flakes. <i>Journal of Physics Condensed Matter</i> , 2020, 32, 12LT01.	1.8	4
12	Wafer-scale production of patterned transition metal ditelluride layers for two-dimensional metal-semiconductor contacts at the Schottky-Mott limit. <i>Nature Electronics</i> , 2020, 3, 207-215.	26.0	91
13	Evidence of tunable magnetic coupling in hydrogenated graphene. <i>Physical Review B</i> , 2020, 102, .	3.2	4
14	Photocurrent response of type-II Dirac semimetal PtTe ₂ . <i>2D Materials</i> , 2020, 7, 034003.	4.4	24
15	Quantum Spin Hall Materials. <i>Advanced Quantum Technologies</i> , 2019, 2, 1900026.	3.9	6
16	Reliable Nonvolatile Memory Black Phosphorus Ferroelectric Field-Effect Transistors with van der Waals Buffer. <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 42358-42364.	8.0	8
17	Gate tunable giant anisotropic resistance in ultra-thin GaTe. <i>Nature Communications</i> , 2019, 10, 2302.	12.8	72
18	Wafer-Scale Growth of Single-Crystal 2D Semiconductor on Perovskite Oxides for High-Performance Transistors. <i>Nano Letters</i> , 2019, 19, 2148-2153.	9.1	82

#	ARTICLE	IF	CITATIONS
19	Nonlinear photoresponse of type-II Weyl semimetals. <i>Nature Materials</i> , 2019, 18, 476-481.	27.5	185
20	Robust edge photocurrent response on layered type II Weyl semimetal WTe ₂ . <i>Nature Communications</i> , 2019, 10, 5736.	12.8	69
21	Micro-MOKE with optical interference in the study of 2D Cr ₂ Ge ₂ Te ₆ nanoflake based magnetic heterostructures. <i>AIP Advances</i> , 2019, 9, .	1.3	4
22	Anisotropic Broadband Photoresponse of Layered Type-II Weyl Semimetal MoTe ₂ . <i>Advanced Materials</i> , 2018, 30, e1707152.	21.0	139
23	Broadband Anisotropic Photoresponse of the "Hydrogen Atom"-Version Type-II Weyl Semimetal Candidate TaIrTe ₄ . <i>ACS Nano</i> , 2018, 12, 4055-4061.	14.6	94
24	Liquid phase mass production of air-stable black phosphorus/phospholipids nanocomposite with ultralow tunneling barrier. <i>2D Materials</i> , 2018, 5, 025012.	4.4	4
25	Barkhausen effect in the first order structural phase transition in type-II Weyl semimetal MoTe ₂ . <i>2D Materials</i> , 2018, 5, 044003.	4.4	12
26	Solution-Based Property Tuning of Black Phosphorus. <i>ACS Applied Materials & Interfaces</i> , 2018, 10, 39890-39897.	8.0	16
27	Electronic transport properties of Co cluster-decorated graphene. <i>Chinese Physics B</i> , 2018, 27, 067304.	1.4	8
28	Ultraviolet Light-Induced Persistent and Degenerated Doping in MoS ₂ for Potential Photocontrollable Electronics Applications. <i>ACS Applied Materials & Interfaces</i> , 2018, 10, 27840-27849.	8.0	13
29	Raman Signatures of Broken Inversion Symmetry and In-Plane Anisotropy in Type-II Weyl Semimetal Candidate TaIrTe ₄ . <i>Advanced Materials</i> , 2018, 30, e1706402.	21.0	54
30	Gate tunable magneto-resistance of ultra-thin W _{1-x} Te ₂ devices. <i>2D Materials</i> , 2017, 4, 021018.	4.4	13
31	Electrically Tunable Energy Bandgap in Dual-Gated Ultra-Thin Black Phosphorus Field Effect Transistors. <i>Chinese Physics Letters</i> , 2017, 34, 047304.	3.3	13
32	Gate-controlled reversible rectifying behaviour in tunnel contacted atomically-thin MoS ₂ transistor. <i>Nature Communications</i> , 2017, 8, 970.	12.8	68
33	Nonlinear transport of graphene in the quantum Hall regime. <i>2D Materials</i> , 2017, 4, 015003.	4.4	4
34	On the Quantum Spin Hall Gap of Monolayer 1Tâ€²WTe ₂ . <i>Advanced Materials</i> , 2016, 28, 4845-4851.	21.0	141
35	Controlled growth of a line defect in graphene and implications for gate-tunable valley filtering. <i>Physical Review B</i> , 2014, 89, .	3.2	117
36	Thickness and growth-condition dependence of in-situ mobility and carrier density of epitaxial thin-film Bi ₂ Se ₃ . <i>Applied Physics Letters</i> , 2014, 105, 173506.	3.3	18

#	ARTICLE	IF	CITATIONS
37	Nanostructures on graphene using supramolecule and supramolecular nanocomposites. <i>Nanoscale</i> , 2014, 6, 4503-4507.	5.6	5
38	In Situ High Temperature Atomic Resolution Transmission Electron Microscopy of 2D Nanomaterials. <i>Microscopy and Microanalysis</i> , 2014, 20, 1770-1771.	0.4	0
39	Atomic Resolution Imaging of Grain Boundary Defects in Monolayer Chemical Vapor Deposition-Grown Hexagonal Boron Nitride. <i>Journal of the American Chemical Society</i> , 2013, 135, 6758-6761.	13.7	225
40	In situ monitoring of resistivity and carrier concentration during molecular beam epitaxy of topological insulator Bi_2Se_3 . <i>Proceedings of SPIE</i> , 2013, , .	0.8	2
41	Reply to "Origin of logarithmic resistance correction in graphene". <i>Nature Physics</i> , 2012, 8, 353-353.	16.7	15
42	Tunable Kondo effect in graphene with defects. <i>Nature Physics</i> , 2011, 7, 535-538.	16.7	353
43	Uncovering the dominant scatterer in graphene sheets on SiO_2 . <i>Physical Review B</i> , 2010, 82, .	3.2	47
44	High-Fidelity Conformation of Graphene to SiO_2 Topographic Features. <i>Physical Review Letters</i> , 2010, 105, 215504.	7.8	118
45	Charged impurity scattering in bilayer graphene. <i>Physical Review B</i> , 2010, 82, .	3.2	81
46	Diffusive charge transport in graphene on SiO_2 . <i>Solid State Communications</i> , 2009, 149, 1080-1086.	1.9	92
47	Scattering mechanisms in graphene. , 2009, , .		0
48	Defect Scattering in Graphene. <i>Physical Review Letters</i> , 2009, 102, 236805.	7.8	566
49	Tuning the Effective Fine Structure Constant in Graphene: Opposing Effects of Dielectric Screening on Short- and Long-Range Potential Scattering. <i>Physical Review Letters</i> , 2008, 101, 146805.	7.8	321
50	Intrinsic and extrinsic performance limits of graphene devices on SiO_2 . <i>Nature Nanotechnology</i> , 2008, 3, 206-209.	31.5	2,730
51	Charged-impurity scattering in graphene. <i>Nature Physics</i> , 2008, 4, 377-381.	16.7	1,318
52	Transfer printing as a method for fabricating hybrid devices on flexible substrates. , 2007, 6658, 141.		8
53	Printed Graphene Circuits. <i>Advanced Materials</i> , 2007, 19, 3623-3627.	21.0	278
54	Atomic Structure of Graphene on SiO_2 . <i>Nano Letters</i> , 2007, 7, 1643-1648.	9.1	1,392

#	ARTICLE	IF	CITATIONS
55	Hooge's constant for carbon nanotube field effect transistors. Applied Physics Letters, 2006, 88, 203116.	3.3	89
56	Electrical Transport in Graphene: Carrier Scattering by Impurities and Phonons. , 0, , 25-37.		0